



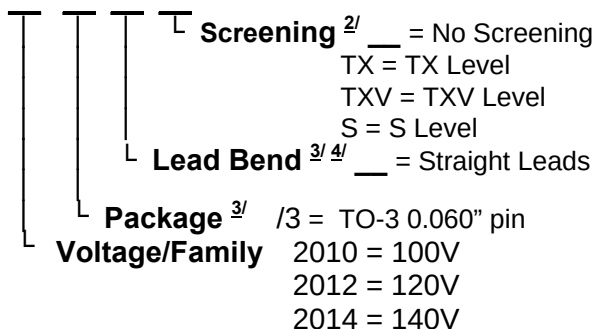
Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, CA 90638
Phone: (562) 404-4474 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

DESIGNER'S DATA SHEET

Part Number / Ordering Information ^{1/}

SFT



SFT2010 thru SFT2014

200 AMP
100 – 140 Volt
High Energy
NPN Transistor

Features:

- $BV_{CBO} = 250 \text{ V MIN}$
- 600 Watts Power Dissipation
- Excellent SOA Curve
- E_s/b of 800mJ
- Gain of over 5 at 200A
- High Reliability Construction
- Planar Chip Construction with Low Leakage and Very Fast Switching
- TX, TXV, S-Level Screening Available^{2/} - Consult Factory

Maximum Ratings		Symbol	Value	Units
Collector – Emitter Voltage	SFT2010 SFT2012 SFT2014	V_{CEO}	100 120 140	Volts
Collector – Base Voltage		V_{CBO}	250	Volts
Emitter – Base Voltage		V_{EBO}	8	Volts
Collector Current		I_C	200	Amps
Base Current		I_B	75	Amps
Total Device Dissipation	$T_C = 50^\circ\text{C}$ Derate above 50°C	P_D	600 4	Watts W/ $^\circ\text{C}$
Operating & Storage Temperature		T_J & T_{STG}	-65 to +200	$^\circ\text{C}$
Maximum Thermal Resistance (Junction to Case)		$R_{\theta JC}$	0.25	$^\circ\text{C/W}$

NOTES: *Pulse Test: Pulse Width = 300μsec, Duty Cycle = 2%

^{1/} For Ordering Information, Price, and Availability Contact Factory.

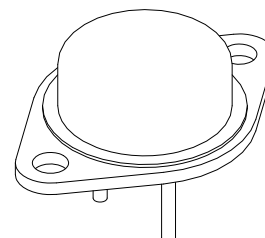
^{2/} Screening per MIL-PRF-19500.

^{3/} For Package Outlines Contact Factory.

^{4/} Up and Down Bend Configurations are Available for 'M' (TO-254) Packages Only.

^{5/} Unless Otherwise Specified, All Electrical Characteristics @25°C.

TO-3



NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0108A

DOC



Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, CA 90638

Phone: (562) 404-4474 * Fax: (562) 404-1773

ssdi@ssdi-power.com * www.ssdi-power.com

SFT2010 thru SFT2014

Electrical Characteristics			Symbol	Min	Max	Units
Collector – Emitter Breakdown Voltage *	(I _C = 200 mA)	SFT2010 SFT2012 SFT2014	BV _{CEO}	100 120 140	—	Volts
Collector – Base Breakdown Voltage *	(I _C = 100μA)		BV _{CBO}	250	—	Volts
Emitter – Base Breakdown Voltage *	(I _E = 100μA)		BV _{EBO}	8	—	Volts
Collector Cutoff Current	(V _{CB} = 250 V)		I _{CBO}	—	10	μA
Emitter Cutoff Current	(V _{EB} = 7 V)		I _{EBO}	—	10	μA
DC Current Gain *	I _C = 10 A, V _{CE} = 2 V I _C = 100 A, V _{CE} = 5 V I _C = 200 A, V _{CE} = 5 V		h _{FE}	40 30 5	—	
Collector-Emitter Saturation Voltage *	(I _C = 120 A, I _B = 12 A) (I _C = 200 A, I _B = 30 A)		V _{CE (SAT)}	— —	2.0 3.0	Volts
Base-Emitter Saturation Voltage *	(I _C = 120 A, I _B = 12 A)		V _{BE (SAT)}	—	2.2	Volts
Current – Gain – Bandwidth Product	(I _C = 1.0 A, V _{CE} = 10 V, f = 10MHz)		f _T	30	—	Mhz
Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1.0MHz		C _{ob}	—	1200	pF
RB SOA	I _B = 1 A, R _{B1} = R _{B2} = 20 ohms V _{BE(off)} = 2.0 V, L = 1.0 mH		E _{s/b}	800	—	mJ
FB SOA	V _{CE} = 20 V, I _C = 30 A V _{CE} = 100 V, I _C = 0.75 A		I _{s/b}	1 1	—	sec
On Time			t _(on)	—	800	ns
Storage Time	(V _{CC} = 60 V, I _C = 10 A, I _{B1} = I _{B2} = 1.0 A)		t _s	—	1500	ns
Fall Time			t _f	—	400	ns

